

**PATENT**

Atty Docket No.: 200310026-1

App. Ser. No.: 10/776,061

**IN THE SPECIFICATION:***Please amend the paragraph beginning on page 1, line 18 as follows:*

In general, the MRAM cells include a data layer and a reference layer. The data layer is composed of a magnetic material and during a write operation the magnetisation magnetization of the data layer can be switched between two opposing states by an applied magnetic field and thus binary information can be stored. The reference layer usually is composed of a magnetic material in which the ~~magnetisation~~-magnetization is pinned so that the magnetic field that is applied to the data layer and in part penetrates the reference layer, is of insufficient strength to switch the ~~magnetisation~~-magnetization in the reference layer.

*Please amend the paragraph beginning on page 6, line 15 as follows:*

The thin dielectric layer 210 is thin enough so that a tunneling current will flow through the dielectric layer when a suitable electrical potential is applied. The tunneling probability, and therefore the impedance of the memory cell, depends on the direction of the magnetization in the data layer 208 ~~[[212]]~~ relative to that of the reference layer 212 ~~[[208]]~~. Therefore, it is possible to determine the orientation of the magnetization in the data layer from the tunneling current which is dependent on the resistance of the memory cell 102.